NTTFS4932NTAG-VB Datasheet

N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω) Typ.	I_D (A)	Q_g (Typ.)
30	0.004 at V_{GS} = 4.5 V	60	33.5 nC
	0.005 at V_{GS} = 2.5 V	50	

FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

RoHS COMPLIANT

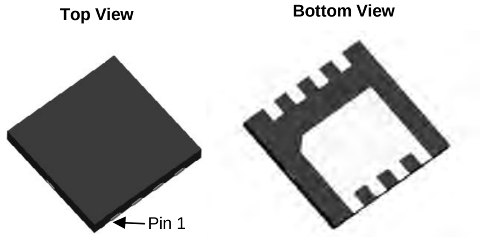
APPLICATIONS

- Motor Control
- Industrial
- Load Switch
- ORing

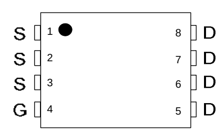
DFN 3x3 EP

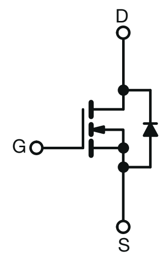
Top View

Bottom View



Top View





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	60[a, e]	A
	T_C = 70 °C		40[a, e]	
	T_A = 25 °C		22[b, c]	
	T_A = 70 °C		15[b, c]	
Pulsed Drain Current (t = 300 µs)		I_{DM}	150	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	35	
	T_A = 25 °C		3.3[b, c]	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	20	
Single Pulse Avalanche Energy		E_{AS}	20	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	52	W
	T_C = 70 °C		33	
	T_A = 25 °C		3.7[b, c]	
	T_A = 70 °C		2.4[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature)			260	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[b, d]	t ≤ 10 s	R_{thJA}	24	33	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.9	2.4	

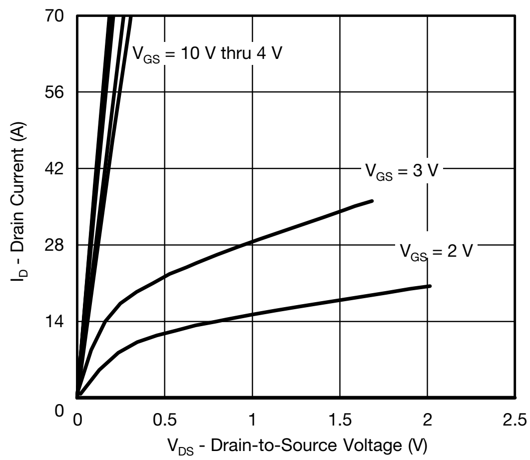
Notes:
a. Based on T_C = 25 °C.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 10 s.
d. Maximum under steady state conditions is 90 °C/W.
e. Calculated based on maximum junction temperature. Package limitation current is 80 A.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		30		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 5.6		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS} , I_D = 250 µA	0.5		1.5	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V			1	µA
		V_{DS} = 30 V, V_{GS} = 0 V, T_J = 55 °C			10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 10 V	30			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 4.5 V, I_D = 10 A		0.0040		Ω
		V_{GS} = 2.5 V, I_D = 7 A		0.0050		
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 10 A		65		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz		6000		pF
Output Capacitance	C_{oss}			406		
Reverse Transfer Capacitance	C_{rss}			360		
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 10 V, I_D = 10 A		68	102	nC
		V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 10 A		33.5	51	
Gate-Source Charge	Q_{gs}			7.7		
Gate-Drain Charge	Q_{gd}			13.8		
Gate Resistance	R_g	f = 1 MHz	0.3	0.7	1.4	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 1.5 Ω $I_D \cong$ 10 A, V_{GEN} = 4.5 V, R_g = 1 Ω		24	45	ns
Rise Time	t_r			24	45	
Turn-Off Delay Time	$t_{d(off)}$			32	60	
Fall Time	t_f			12	24	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 1.5 Ω $I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω		14	28	
Rise Time	t_r			13	26	
Turn-Off Delay Time	$t_{d(off)}$			33	60	
Fall Time	t_f			8	16	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C		35		A
Pulse Diode Forward Current	I_{SM}			70		
Body Diode Voltage	V_{SD}	I_S = 3 A, V_{GS} = 0 V		0.7	1.1	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 10 A, dI/dt = 100 A/µs, T_J = 25 °C		21	40	ns
Body Diode Reverse Recovery Charge	Q_{rr}			10	20	nC
Reverse Recovery Fall Time	t_a			9		ns
Reverse Recovery Rise Time	t_b			12		

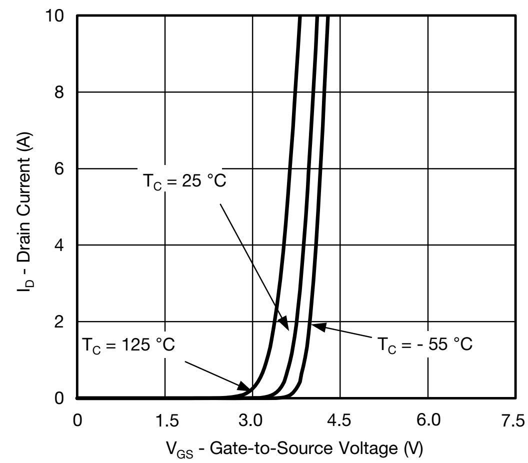
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

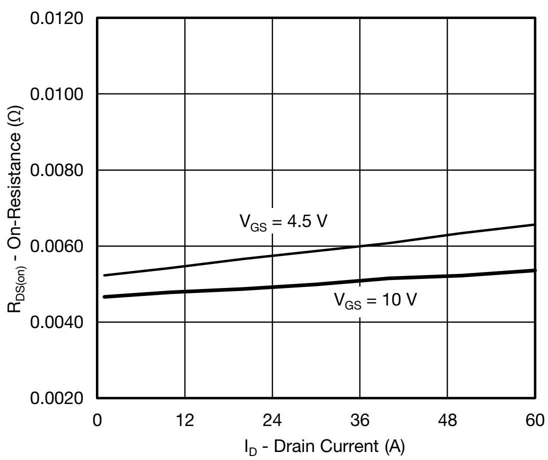
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



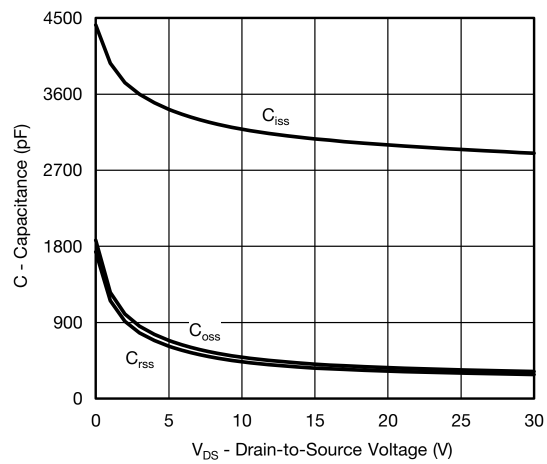
Output Characteristics



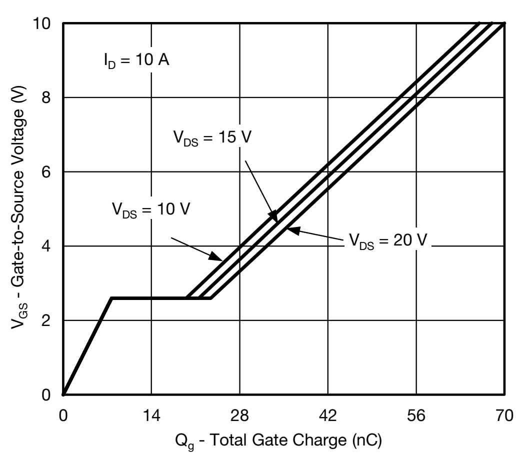
Transfer Characteristics



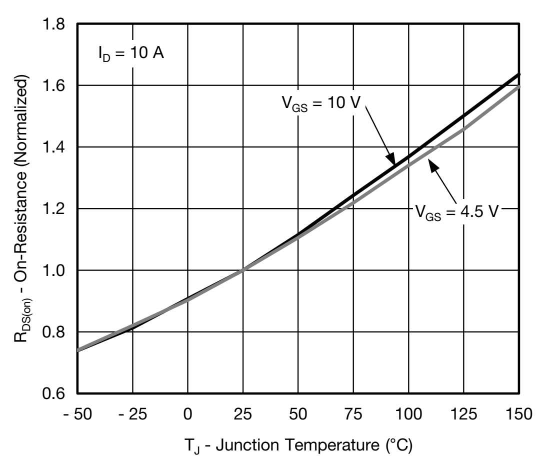
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

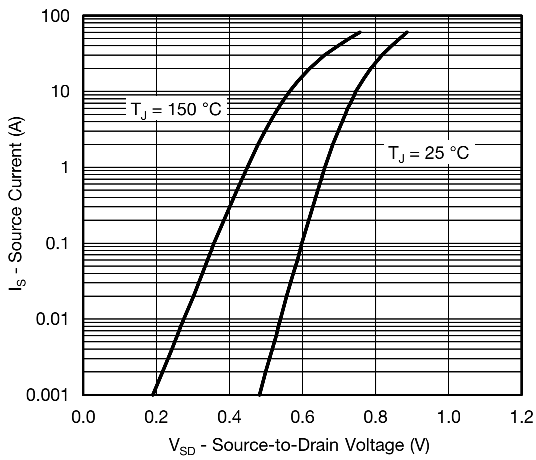


Gate Charge

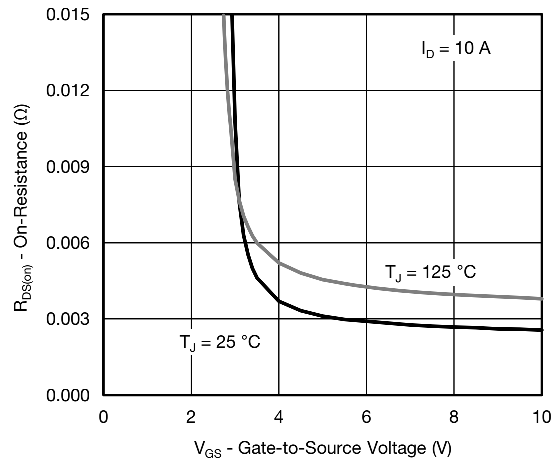


On-Resistance vs. Junction Temperature

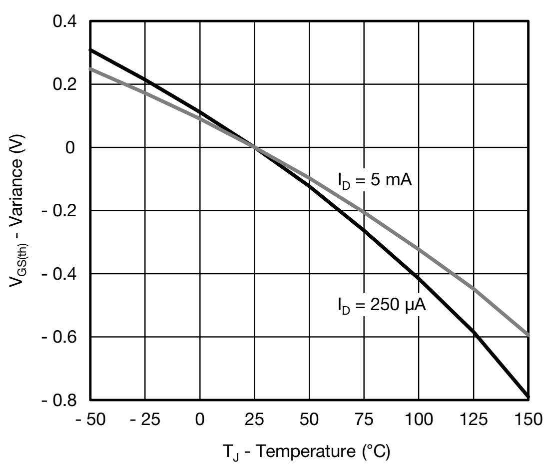
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



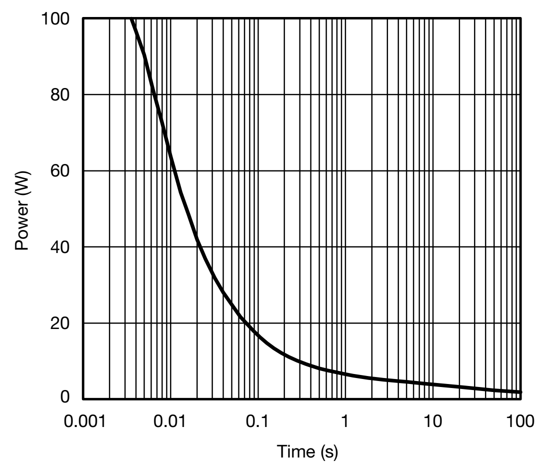
Source-Drain Diode Forward Voltage



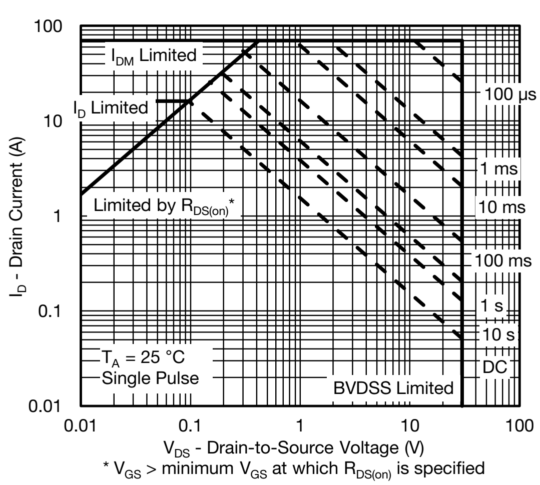
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

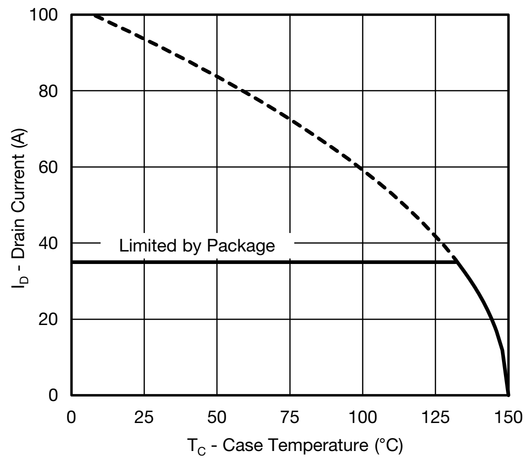


Single Pulse Power, Junction-to-Ambient

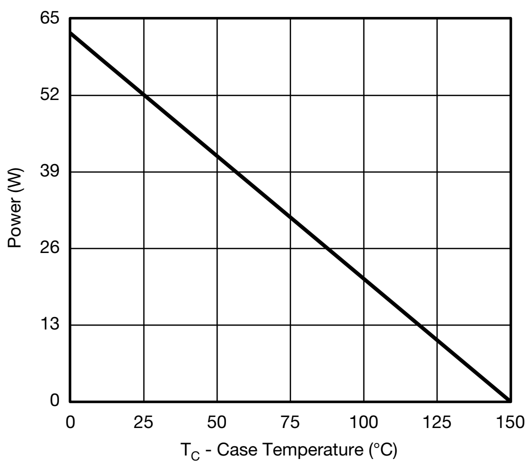


Safe Operating Area, Junction-to-Ambient

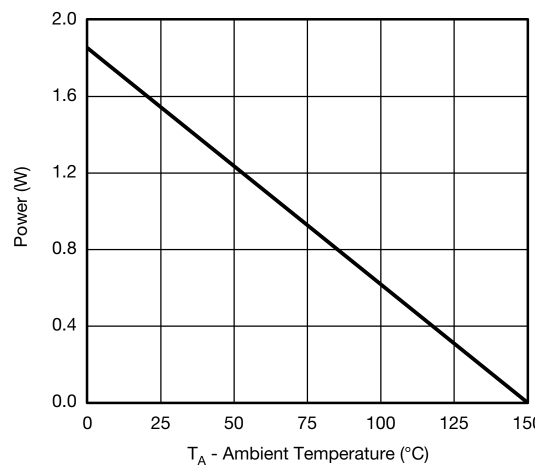
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



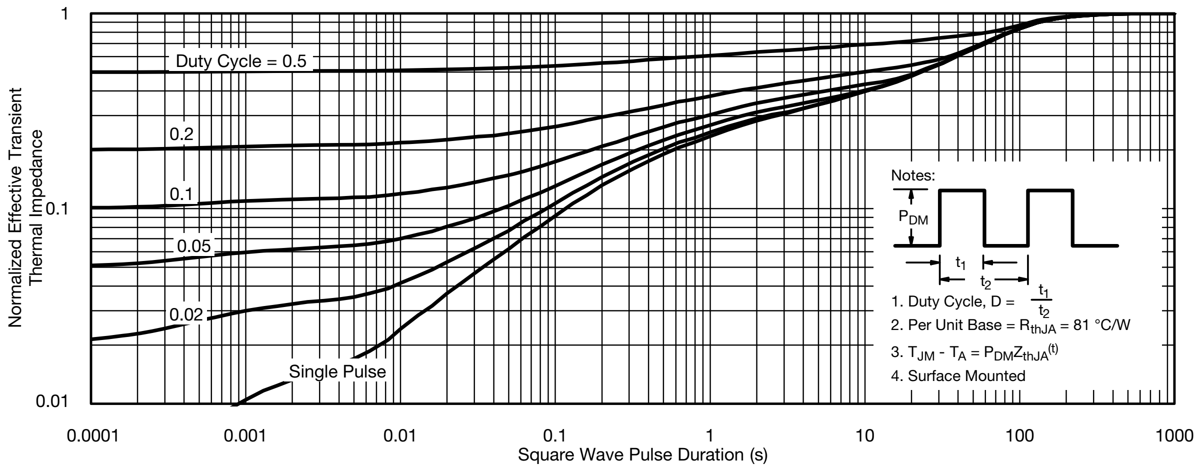
Power, Junction-to-Case



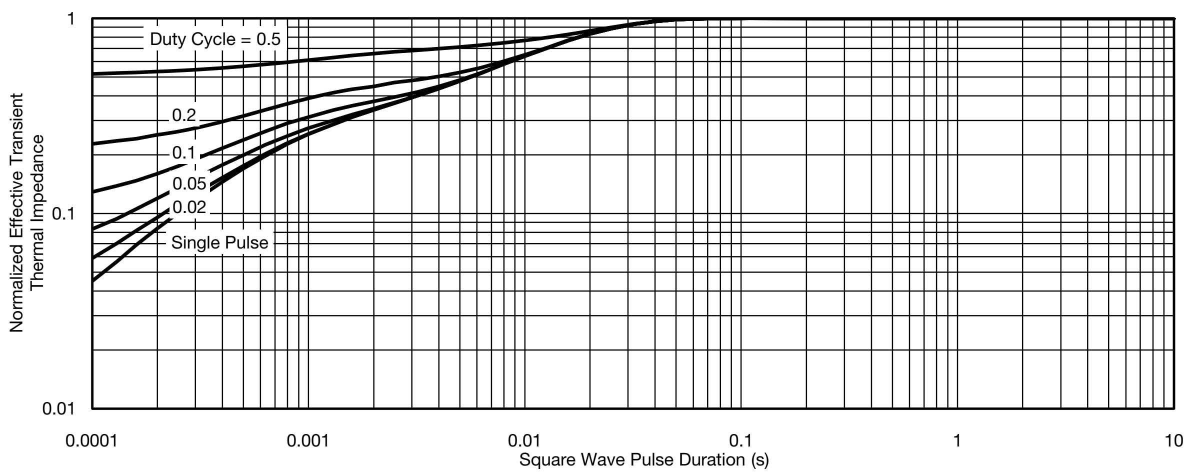
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

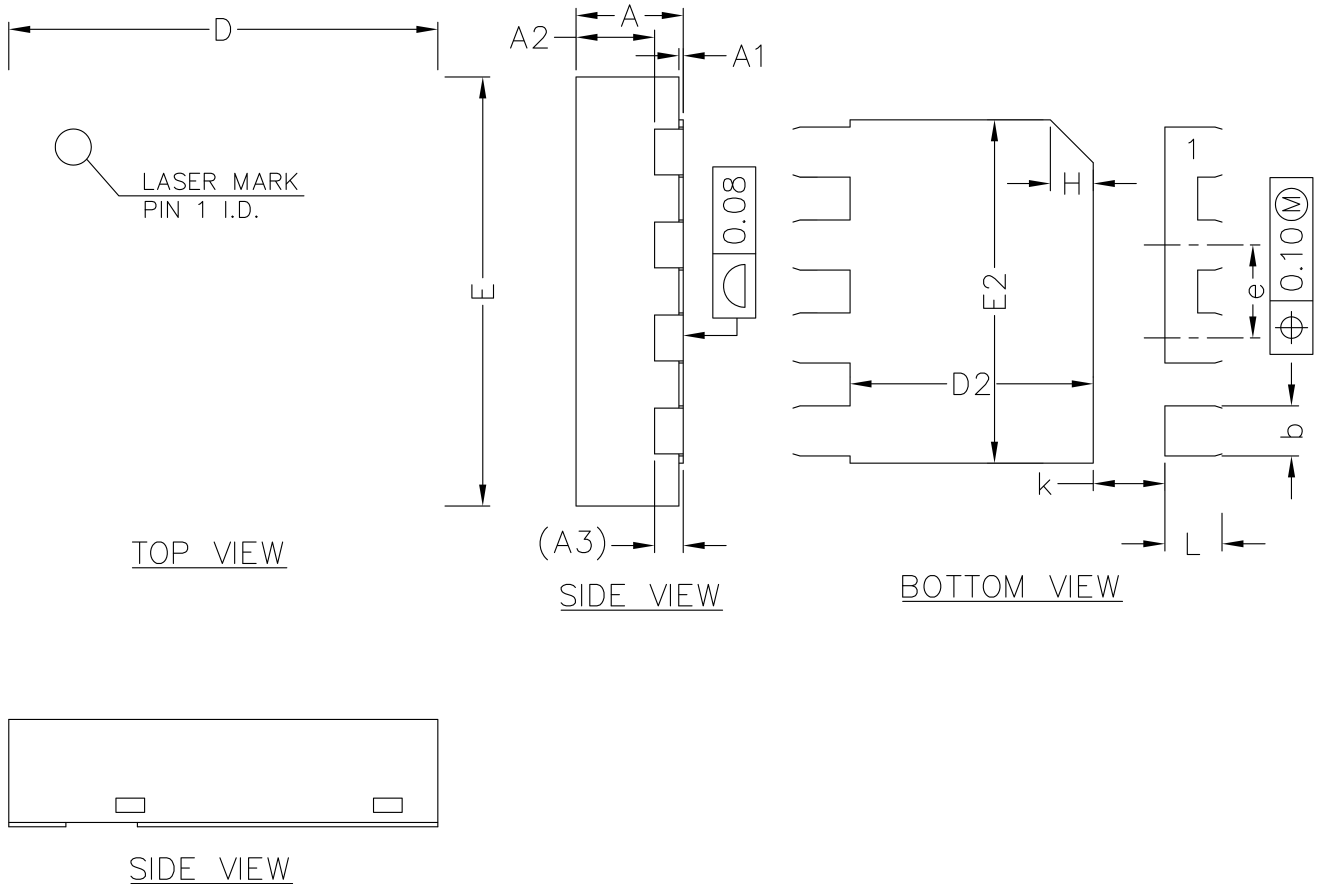
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
A2	0.50	0.55	0.60
A3	0.20REF		
b	0.30	0.35	0.40
D	2.90	3.00	3.10
E	2.90	3.00	3.10
D2	1.60	1.70	1.80
E2	2.30	2.40	2.50
e	0.55	0.65	0.75
K	0.40	0.50	0.60
L	0.35	0.40	0.45

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